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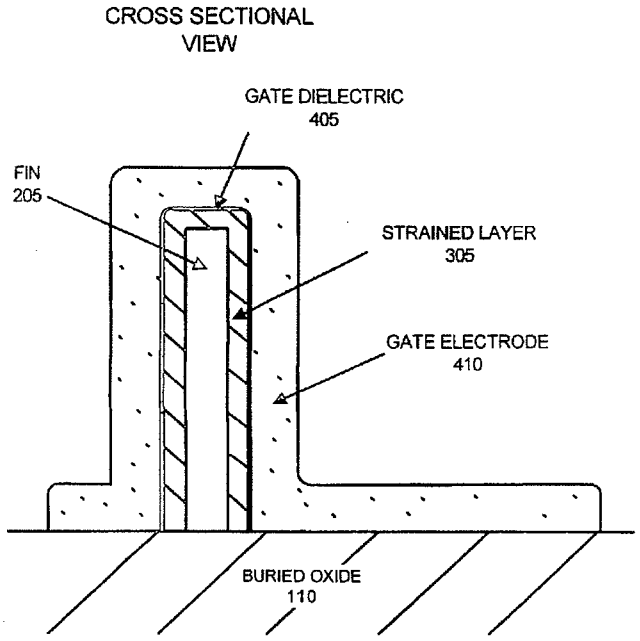
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(54) Title: STRAINED CHANNEL FINFET



(57) Abstract: A semiconductor structure includes a fin (205) and a layer (305) formed on the fin. The fin (205) includes a first crystalline material having a rectangular cross section and a number of surfaces. The layer (305) is formed on the surfaces and includes a second crystalline material. The first crystalline material has a different lattice constant than the second crystalline material to induce tensile strain within the layer (305).

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